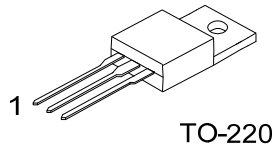
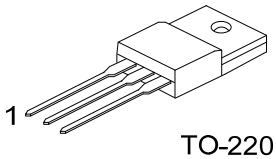
18A, 1000V N-CHANNEL SUPER-JUNCTION MOSFET



TO-220



TO-220F1

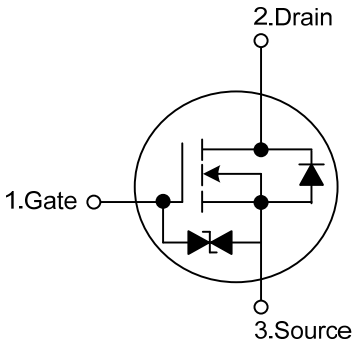
■ DESCRIPTION

The UTC **18NM100SZ** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

■ FEATURES

* $R_{DS(ON)} \leq 0.43\ \Omega$ @ V_{GS}=10V, I_D=6.0A
* Fast switching capability
* Avalanche energy tested
* Improved dv/dt capability, high ruggedness
* With ESD protection

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
18NM100SZL-TA3-T	18NM100SZG-TA3-T	TO-220	G	D	S	Tube
18NM100SZL-TF1-T	18NM100SZG-TF1-T	TO-220F1	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

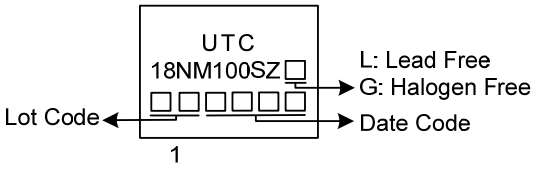
18NM100SZG-TA3-T

(1)Packing Type — (1) T: Tube

(2)Package Type — (2) TA3: TO-220, TF1: TO-220F1

(3)Green Package — (3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATING (T_C=25°C unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	1000	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	DC	I_D	18	A
	Pulsed (Note 2)	I_{DM}	54	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	650	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	0.97	V/ns
Power Dissipation	TO-220	P_D	125	W
	TO-220F1		34	W
Junction Temperature		T_J	+150	°C
Storage Temperature Range		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 100mH, I_{AS} = 3.6A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C.
4. I_{SD} ≤ 18A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C.

■ THERMAL DATA

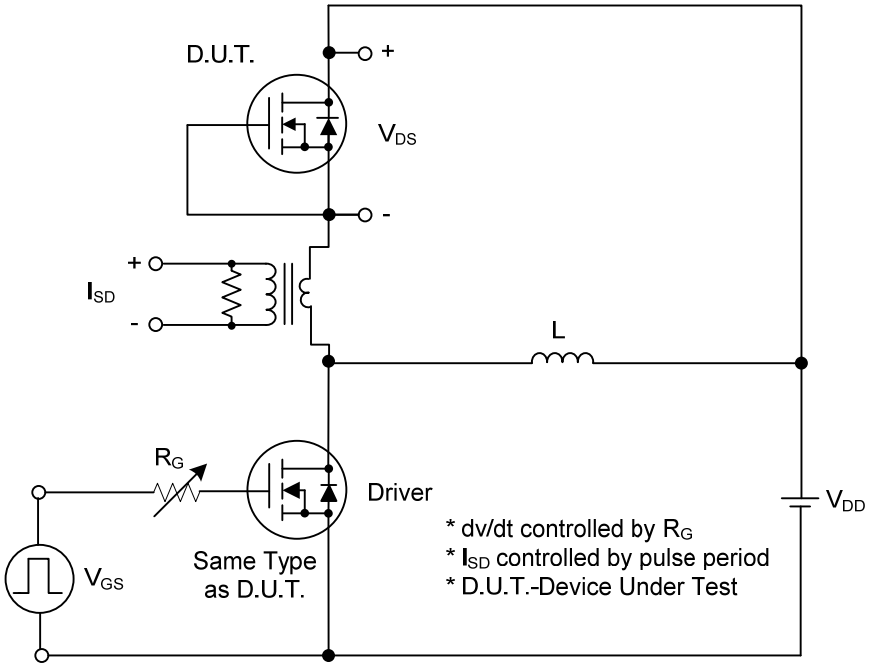
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	°C/W
Junction to Case	TO-220	θ_{JC}	1	°C/W
	TO-220F1		3.6	°C/W

■ ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise specified)

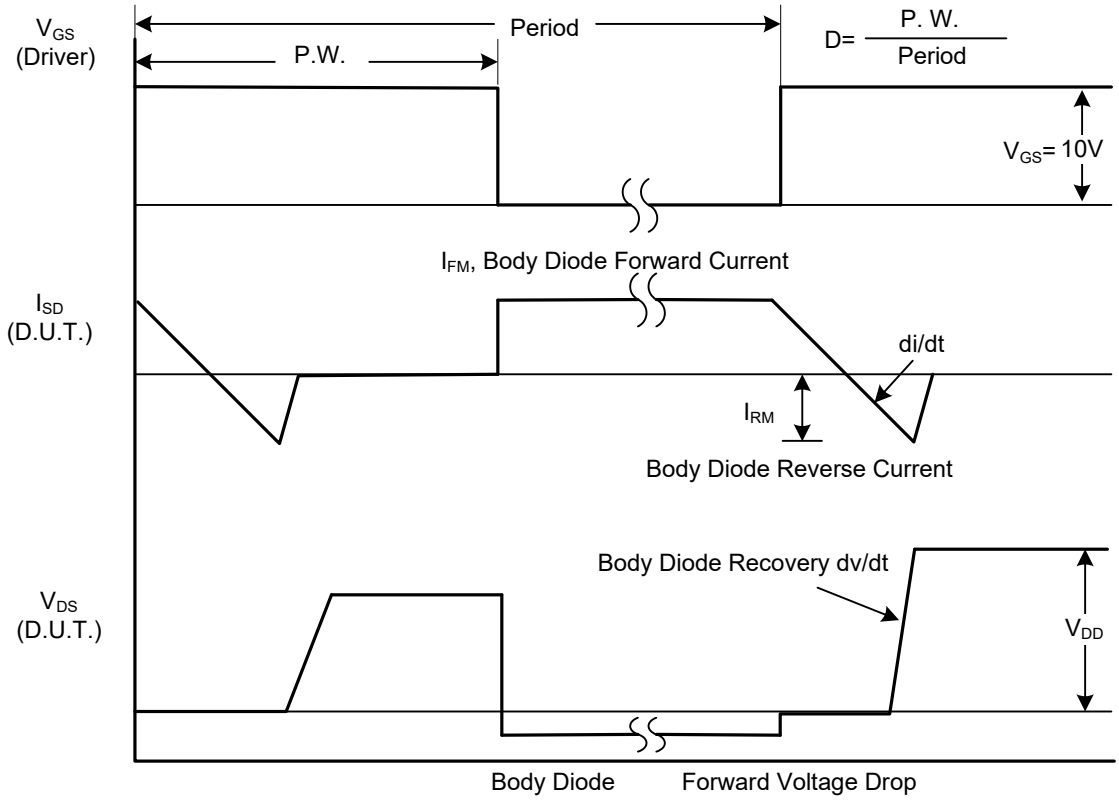
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=250μA	1000			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=1000V, V_{GS}=0V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=+20V, V_{DS}=0V			+10	μA
	Reverse		V_{GS}=-20V, V_{DS}=0V			-10	μA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=6.0A			0.43	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=50V, f=1.0MHz		1600		pF
Output Capacitance		C_{OSS}			96		pF
Reverse Transfer Capacitance		C_{RSS}			3		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{DS}=760V, V_{GS}=10V, I_D=18A (Note 1, 2)		45		nC
Gate to Source Charge		Q_{GS}			12		nC
Gate to Drain Charge		Q_{GD}			11		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=100V, V_{GS}=10V, I_D=18A, R_G=25Ω (Note 1, 2)		16		ns
Rise Time		t_R			22		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			120		ns
Fall-Time		t_F			53		ns
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I_S				18	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				54	A
Diode Forward Voltage		V_{SD}	I_F=18A, V_{GS}=0V			1.4	V
Reverse Recovery Time		t_{rr}	I_S=18A, V_{GS}=0V, dI_F/dt = 100 A/μs		560		ns
Reverse Recovery Charge (Note 1)		Q_{rr}			11.3		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

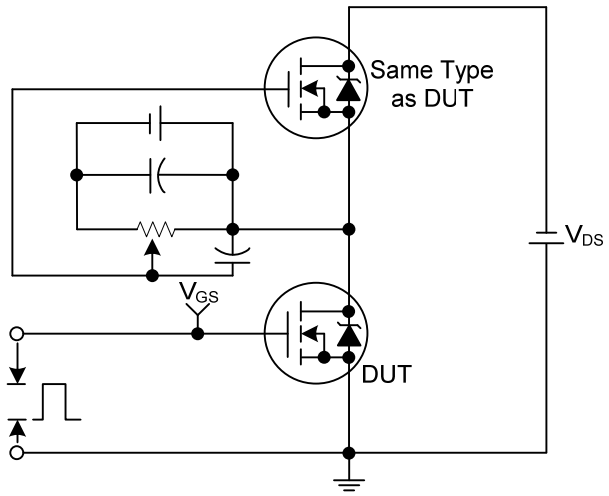


Peak Diode Recovery dv/dt Test Circuit

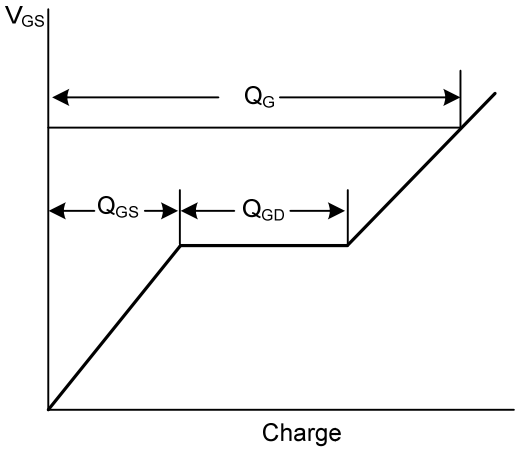


Peak Diode Recovery dv/dt Waveforms

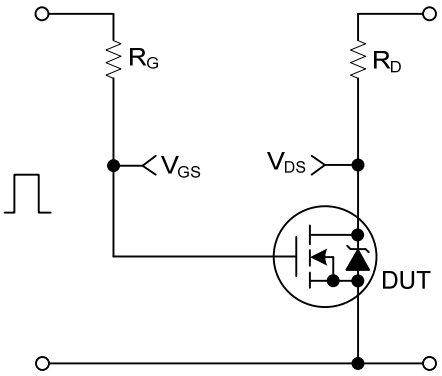
■ TEST CIRCUITS AND WAVEFORMS



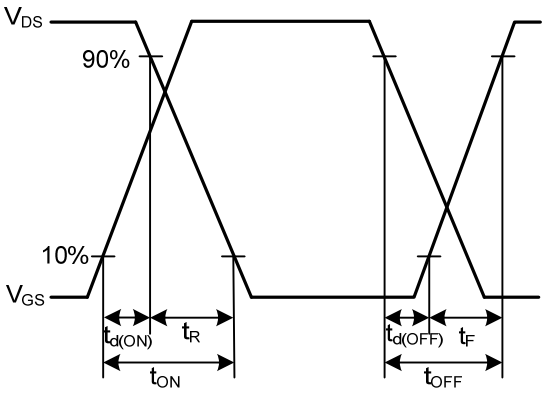
Gate Charge Test Circuit



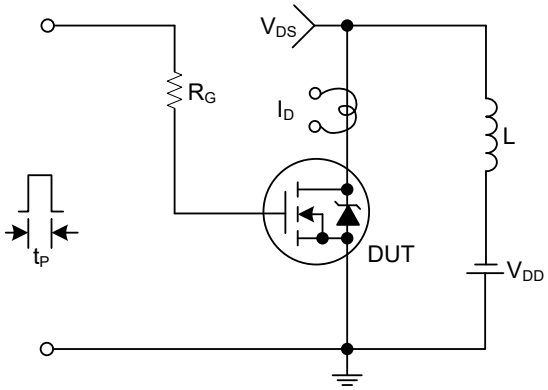
Gate Charge Waveforms



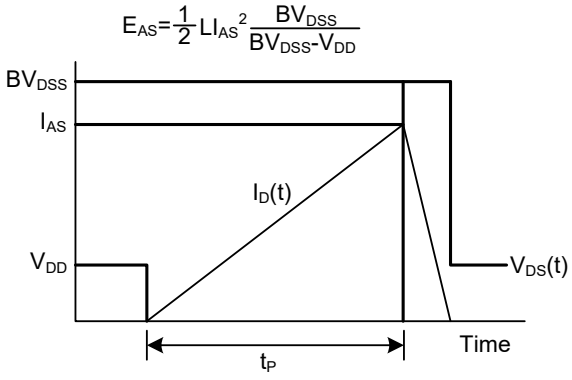
Resistive Switching Test Circuit



Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms